Applied Semiconductor Physics

Module coordinator
Managing Director of the Institute of Applied Physics

Module offered by
Faculty of Physics and Astronomy

ECTS
6

Method of grading
Only after succ. compl. of module(s)

Numerical grade
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Duration
1 semester

Module level
graduate

Other prerequisites
Certain prerequisites must be met to qualify for admission to assessment. The lecturer will inform students about the respective details at the beginning of the course. Registration for the course will be considered a declaration of will to seek admission to assessment. If students have obtained the qualification for admission to assessment over the course of the semester, the lecturer will put their registration for assessment into effect. Students who meet all prerequisites will be admitted to assessment in the current or in the subsequent semester. For assessment at a later date, students will have to obtain the qualification for admission to assessment anew.

Contents
The lecture discusses the principles of Semiconductor Physics and provides an exemplary overview of the main components of electronics, optoelectronics and photonics.

Intended learning outcomes
The students know the characteristics of semiconductors, they have gained an overview of the electronic and phonon band structures of important semiconductors and the resulting electronic, optical and thermal properties. They know the principles of charge transport as well as the Poisson, Boltzmann and continuity equation for the solution of questions. They have gained insights into the methods of semiconductor production and are familiar with the theories of planar technology and recent developments in this field, they have a basic understanding of component production. They understand the structure and way of functioning of the main components of electronics (diode, transistor, field-effect transistor, thyristor, diac, triac), of microwave applications (tunnel, Impatt, Baritt or Gunn diode) and of optoelectronics (photo diode, solar cell, light-emitting diode, semiconductor injection laser), they know the realisation possibilities of low-dimensional charge carrier systems on the basis of semiconductors and their technological relevance, they are familiar with current developments in the field of components.

Courses
R + V (no information on SWS (weekly contact hours) and course language available)

Method of assessment
a) written examination (approx. 90 minutes) or b) oral examination of one candidate each or oral examination in groups (approx. 30 minutes per candidate, for modules with less than 4 ECTS credits approx. 20 minutes) or c) project report (approx. 8 to 10 pages, time to complete: 1 to 4 weeks) or d) presentation/seminar presentation (approx. 30 minutes)

Assessment offered: When and how often assessment will be offered depends on the method of assessment and will be announced in due form under observance of Section 32 Subsection 3 ASPO (general academic and examination regulations) 2009.

Language of assessment: German, English

Allocation of places
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Additional information
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**Module description**

**Referred to in LPO I** (examination regulations for teaching-degree programmes)

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<th>Module appears in</th>
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<tr>
<td>Bachelor’ degree (1 major) Physics (2010)</td>
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<td>Bachelor’ degree (1 major) Nanostructure Technology (2010)</td>
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<tr>
<td>Master's degree (1 major) Mathematics (2010)</td>
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